

Amendment to the Specification

Please amend the Abstract as follows.

There is provided a semiconductor device comprising: a first plating layer ~~(30)~~ formed on one surface of an interconnect pattern ~~(21)~~; a second plating layer ~~(32)~~ formed within through holes ~~(28)~~ in the interconnect pattern ~~(21)~~; a semiconductor chip ~~(10)~~ electrically connected to the first plating layer ~~(30)~~; an anisotropic conductive material ~~(34)~~ provided on the first plating layer ~~(30)~~; and a conductive material ~~(36)~~ provided on the second plating layer ~~(32)~~, wherein the first plating layer ~~(30)~~ has appropriate adhesion properties with the anisotropic conductive material ~~(34)~~, and the second plating layer ~~(32)~~ has appropriate adhesion properties with the conductive material ~~(36)~~.